

IN THE CLAIMS:

Kindly amend claim 1 as follows:

Kindly replace claim 1 with the following amended claim 1:

- Initials B3*
- A2*
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1. (Amended) A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, the method comprising the steps of:
depositing a barrier metal on the whole surface of the insulation layer including the substrate surface in the recess region;
depositing selectively an anti-nucleation layer on the barrier metal except in the recess region;
depositing a CVD-Al layer on the barrier metal in the recess region;
depositing a metal or a metal alloy for inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region; and
depositing a PVD-Al layer and reflowing the PVD-Al layer.
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The changes in the previous claim are indicated by brackets for deletions and underlining for insertions.

1. (Amended) A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, the method comprising the steps of:
 - depositing a barrier metal on the whole surface of the insulation layer including the substrate surface in the recess region;
 - depositing selectively an anti-nucleation layer on the barrier metal except in the recess region;
 - depositing a CVD-Al layer on the barrier metal in the recess region;
 - depositing a metal or a metal alloy for inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region; and
 - depositing a PVD-Al layer and reflowing the PVD-Al layer.